

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5274	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/20 21:00
L2	190	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/20 21:08
L3	1054	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/20 21:08
S1	640	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide)	USPAT	OR	ON	2005/03/31 19:21
S2	45	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near electrode and (ITO or indium near tin near oxide) near (layer or film or structure)	USPAT	OR	ON	2005/03/31 19:36
S3	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) with (ITO or indium near tin near oxide) near gate and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S4	0	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) near gate near electrode and (ITO or indium near tin near oxide) near (source or drain)	USPAT	OR	ON	2005/03/31 19:37
S5	82	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16

S6	281	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) same gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S7	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S8	259	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT	OR	ON	2005/03/31 20:16
S9	278	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/12/20 17:29
S10	177	S8 not S5	USPAT; JPO	OR	ON	2005/03/31 20:17
S11	94	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/03/31 20:54
S12	12	S11 not S5	USPAT; JPO	OR	ON	2005/03/31 20:55
S13	2	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with gate near electrode and (ITO or indium near tin near oxide) with (source or drain)	USPAT; JPO	OR	ON	2005/04/01 13:44
S14	6	257/79 and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) same gate near electrode same (source or drain)	USPAT; JPO	OR	ON	2005/04/01 14:29

S15	1215	349/139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:48
S16	899	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:28
S17	528	349/152	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:37
S18	7213	(ITO or indium near tin near oxide) with (residue or remnant or left near over or ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S19	10	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:42
S20	6749	(ITO or indium near tin near oxide) with (ring or enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:47
S21	3375	(ITO or indium near tin near oxide) with (ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:43
S22	221	(ITO or indium near tin near oxide) with (ring) with (wir\$3 or film or layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:44

S23	212	(ITO or indium near tin near oxide) with (ring) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S24	3608	(ITO or indium near tin near oxide) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 15:49
S25	2	(ITO or indium near tin near oxide) with (residue or remnant or left near over) with (enclosur\$3 or surround\$3 or around\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:05
S26	4646	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:15
S27	174	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:28
S28	172	257/749	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:37
S29	5	257/e51.005	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:44
S30	1214	257/79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 16:56

S31	3773	257/347	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:08
S32	1825	257/350	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:18
S33	269	257/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:33
S34	1	257/E33.064	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S35	0	257/E31.126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S36	4	257/E29.151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:34
S37	0	257/E23.157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:35
S38	132	438/609	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:36

S39	2549	174/255	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:37
S40	1044	174/256	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 17:45
S41	807	174/257	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02
S42	938	174/258	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 18:02
S43	1366	349/139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:49
S44	1378	257/79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
S45	10	257/E51.005	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
S46	2	257/E33.064	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03

S47	0	257/E31.126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:03
S48	8	257/E29.151	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:04
S49	0	257/E23.157	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:04
S50	5037	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:29
S51	185	257/449	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:31
S52	191	257/749	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:34
S53	4116	257/347	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 15:34
S54	11360	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide)	USPAT; JPO	OR	ON	2005/12/20 17:29
S55	1955	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide)	USPAT; JPO	OR	ON	2005/12/20 19:02

S56	33	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (surround\$3 or around\$3 or enclosur\$3)	USPAT; JPO	OR	ON	2005/12/20 18:29
S57	209	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (open\$3 or recess or hole or cavity or aperture)	USPAT; JPO	OR	ON	2005/12/20 18:28
S58	208	S57 not S56	USPAT; JPO	OR	ON	2005/12/20 17:41
S59	209	(semiconductor or dice or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (open\$3 or recess or hole or cavity or aperture)	USPAT; JPO	OR	ON	2005/12/20 18:29
S60	33	(semiconductor or dice or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (surround\$3 or around\$3 or enclosur\$3)	USPAT; JPO	OR	ON	2005/12/20 18:29
S61	153	(semiconductor or dice or die or chip or IC) and (TFT-array or "TFT" near array or transistor) and (ITO or indium near tin near oxide) with (surround\$3 or around\$3 or enclosur\$3)	USPAT; JPO	OR	ON	2005/12/20 18:57
S62	1685	S55 not (S56 or S57 or S61)	USPAT; JPO	OR	ON	2005/12/20 18:58
S63	1455	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with electrode	USPAT; JPO	OR	ON	2005/12/20 19:02
S64	1508	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (electrode or gate)	USPAT; JPO	OR	ON	2005/12/20 19:03
S65	176	(semiconductor or die or chip or IC) and (TFT-array or "TFT" near array or transistor) same (ITO or indium near tin near oxide) with (electrode or gate) with (open\$3 or recess or hole or cavity or aperture)	USPAT; JPO	OR	ON	2005/12/20 19:03